



80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
001/	6.9mΩ @ V _{GS} = 10V	52A
80V	10.4mΩ @ V _{GS} = 4.5V	42A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

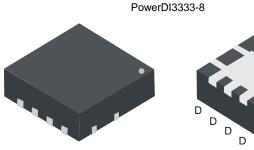
Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH8008LFGQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

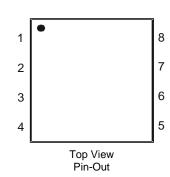
https://www.diodes.com/quality/product-definitions/

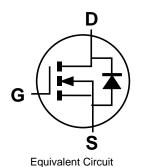
Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208(§3)
- Weight: 0.072 grams (Approximate)









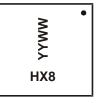
Ordering Information (Note 4)

Part Number	Case	Packaging		
DMTH8008LFGQ-7	PowerDI3333-8	2,000/Tape & Reel		
DMTH8008LFGQ-13	PowerDI3333-8	3,000/Tape & Reel		

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



HX8 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	80	V	
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	$T_C = +25$ °C $T_C = +100$ °C	lo	52 37	Α
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		lo	17 12	А
Maximum Continuous Body Diode Forward Current (Note 6)	Is	45	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	200	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%	I _{SM}	200	Α	
Avalanche Current, L = 1mH (Note 8)	las	18	A	
Avalanche Energy, L = 1mH (Note 8)	E _{AS}	162	mJ	

Thermal Characteristics

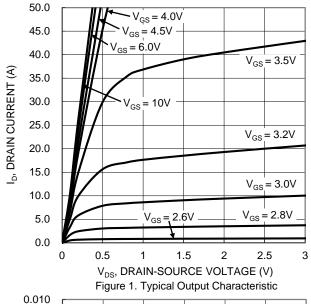
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	126	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	49	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	PD	28.3	W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	5.3	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C	

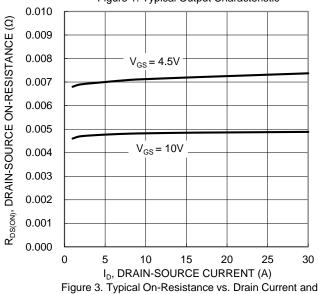
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	80		_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 64V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1.2	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Static Drain-Source On-Resistance	Descent		5.3	6.9	mΩ	Vgs = 10V, ID = 20A	
Static Dialii-Source Off-Resistance	RDS(ON)	_	7.9	10.4		Vgs = 4.5V, ID = 10A	
Diode Forward Voltage	VsD	_	8.0	1.2	V	Vgs = 0V, Is = 20A	
DYNAMIC CHARACTERISTICS (Note 10)	DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	_	2254	_		V _{DS} = 40V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss		745	_	pF		
Reverse Transfer Capacitance	Crss	_	31	_			
Gate Resistance	Rg	_	1.98	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	18.3	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	37.7	_	nC	\/ 40\/ I- 444	
Gate-Source Charge	Qgs	_	5.3	_	iiC	$V_{DS} = 40V, I_{D} = 14A$	
Gate-Drain Charge	Q_{gd}	_	7.8	_		!	
Turn-On Delay Time	t _{D(ON)}		6.9	_			
Turn-On Rise Time	t _R	_	12	_		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 14A, R_{G} = 6\Omega$	
Turn-Off Delay Time	tD(OFF)	_	37	_	ns		
Turn-Off Fall Time	tF	_	21	_			
Body Diode Reverse Recovery Time	trr	_	42	_	ns I 444 division 4004 / co		
Body Diode Reverse Recovery Charge	Qrr	_	53	_	nC	$Is = 14A$, di/dt = 100A/ μ s	

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.







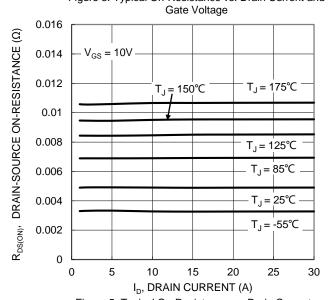
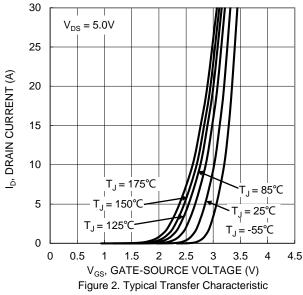
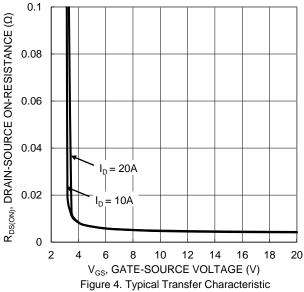


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





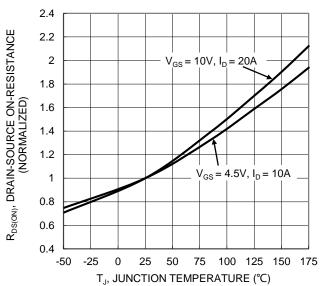


Figure 6. On-Resistance Variation with Temperature





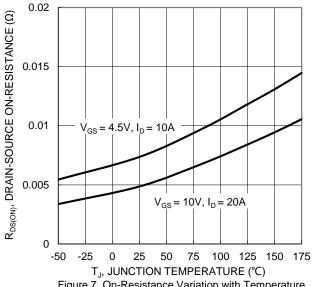


Figure 7. On-Resistance Variation with Temperature

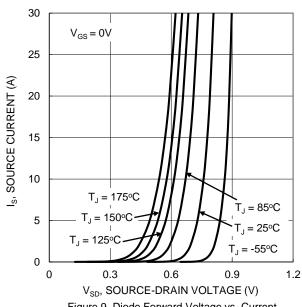


Figure 9. Diode Forward Voltage vs. Current

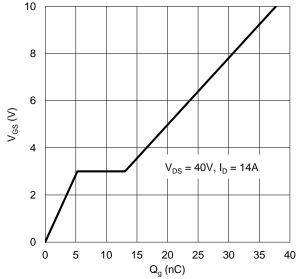


Figure 11. Gate Charge

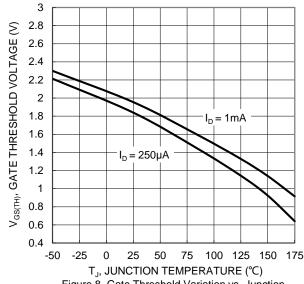


Figure 8. Gate Threshold Variation vs. Junction Temperature

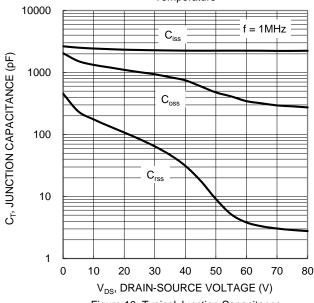


Figure 10. Typical Junction Capacitance

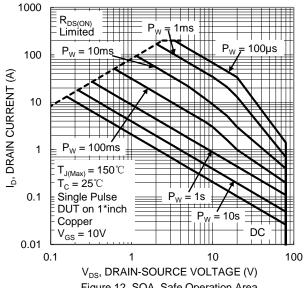


Figure 12. SOA, Safe Operation Area



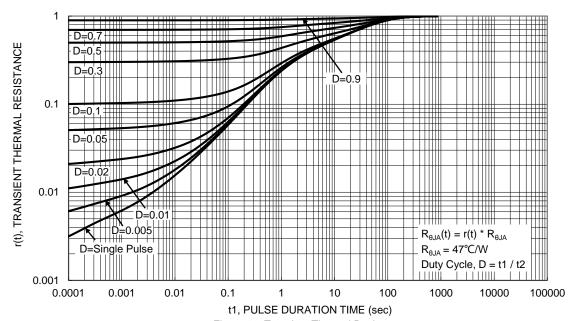


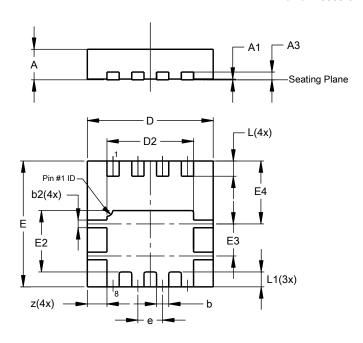
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

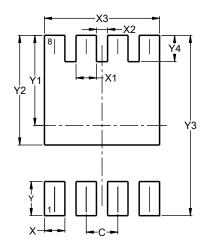


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	_	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	-	-	0.65		
١	0.35	0.45	0.40		
L1	_	_	0.39		
z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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